

Title (en)  
METHOD FOR DEPOSITION OF DENSE CHROMIUM ON A SUBSTRATE

Title (de)  
VERFAHREN ZUR ABSCHIEDUNG VON DICHTEM CHROM AUF EINEM SUBSTRAT

Title (fr)  
PROCEDE DE DEPOT DE CHROME DENSE SUR UN SUBSTRAT

Publication  
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Application  
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Abstract (en)  
[origin: WO2022243611A1] The invention relates to a method for depositing a chromium-based material from a target onto a metal substrate, by continuous magnetron sputtering, using a plasma generated in a gas. According to the invention: the ratio between the flow of gaseous ions directed toward the substrate and the flow of neutral chromium atoms directed toward the substrate is adjusted to between 0.5 and 1.7; and a bias voltage of between -50 V and -100 V is applied to the substrates.

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